

Amendments to the Specification are as follows:

Please amend line 1 as follows:

(Amended) SPECIFICATION

Please amend line 3 as follows:

(Amended) ~~TITLE OF THE INVENTION~~

Please amend the paragraph beginning on page 3, line 6 and ending on page 3, line 26 as follows:

(Amended) The level of the optical output outputted from the semiconductor laser 41 is determined by a sum of the bias electric current and the modulating electric current. Therefore, if the pulse signal for modulation is continuously inputted in the above construction, the modulating electric current and the bias electric current are changed dependently on temperature. Accordingly, the optical output level is controlled by the optical output control circuit 51 such that the optical output level is constant at all times. However, when the pulse signal for modulation is inputted in a so-called burst shape, no modulating electric current is flowed to the semiconductor laser 41 in a period in which no pulse signal for modulation is inputted. Accordingly, no electric current is flowed to the light receiving element 50 so that the optical output control circuit 51 increases the~~intends to flow a maximum~~ electric current to the semiconductor laser 41 to a maximum. As this result, there is a problem of destroying the semiconductor laser 41. Accordingly, no semiconductor laser can be used in the burst mode in the conventional construction.

Please amend the paragraph beginning on page 5, line 23 and ending on page 6, line 4 as follows:

(Amended) Further, the feedback circuit is constructed by a transistor for flowing the bias electric current to the semiconductor laser, a seventh resistor connected between the emitter of the transistor and the ground, and an operational amplifier interposed between the second temperature correcting means and the base of the transistor, and the divided voltage is applied to a non-inversion input terminal of the operational amplifier, and the emitter of the transistor is connected to an inversion input terminal of the operational amplifier.

Please amend the paragraph beginning on page 7, line 23 and ending on page 8, line 10 as follows:

(Amended) For example, at the time of 25 °C, the bias electric current I_{b1} among the required total electric current I_{o1} is supplied at all times, and the demodulating electric current I_{m1} is superposed on this bias electric current. If the temperature rises to 65 °C, the required total electric current I_{o2} , the bias electric current I_{b2} and the demodulating electric current I_{m2} are increased. In Fig. 3, the various electric currents required in the semiconductor laser 1 are calculated by the actual measurement as to how these electric currents are changed in accordance with the temperature. The solid line of A of Fig. 3 shows the total electric current (I_o) and the solid line of B shows the bias electric current (I_b), and the solid line of C shows the demodulating electric current (I_m).